| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|---|---|---|---|---|---|---|
| 1 | IS&R | L1 | 532 | (257/324,326).CCLS. | USPAT; US-PGPUB | 2003/07/21 14:46 |
| 2 | BRS | L2 | 50 | 1 and @pd>20030115 | USPAT; US-PGPUB | 2003/07/21 14:46 |
| 3 | BRS | L5 | 105 | ("3895360" \| "4016588" \| "4017888" \| "4151021" \| "4173766" \| "4173791" \| "4257832" \| "4306353" \| "4342149" \| "4360900" \| "4380057" \| "4471373" \| "4521796" \| "4527257" \| "4586163" \| "4630085" \| "4667217" \| "4742491" \| "4769340" \| "4780424" \| "4847808" \| "4870470" \| "4941028" \| "5021999" \| "5042009" \| "5075245" \| "5104819" \| "5159570" \| "5168334" \| "5172338" \| "5175120" \| "5214303" \| "5260593" \| "5293563" \| "5295108" \| "5305262" \| "5311049" \| "5324675" \| "5338954" \| "5345425" \| "5349221" \| "5350710" \| "5359554" \| "5375094" \| "5393701" \| "5394355" \| "5412601" \| "5414693" \| "5418176" \| "5418743" \| "5422844" \| "5424567" \| "5424978" \| "5426605" \| "5434825" \| "5436481" \| "5440505" \| "5450341" \| "5450354" \| "5455793" \| "5467308" \| "5477499" \| "5496753" \| "5518942" \| "5523251" \| "5553018" \| "5563823" \| "5592417" \| "5599727" \| "5606523" \| "5654568" \| "5656513" \| "5712814" \| "5726946" \| "5751037" \| "5754475" \| "5760445" \| "5768192" \| "5787036" \| "5793079" \| "5801076" \| "5812449" \| "5825686" \| "5836772" \| "5841700" \| "5847441" \| "5864164" \| "5870335" \| "5886927" \| "5903031" \| "5946558" \| "5963412" \| "5973373" \| "5991202" \| "6018186" \| "6020241" \| | USPAT | 2003/07/21 14:54 |

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| 1 | US 5424978 A | 15 | Non-volatile semiconductor memory cell capable of storing more than two different data and method of using the same | 365/184 | 365/185.03; 365/185.19 | Wada, Toshio et al. |
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| 3 | US 5440505 A | 21 | Method and circuitry for storing discrete amounts of charge in a single memory element | 365/45 | 365/185.03; 365/185.22; 365/189.01; 365/218; 365/230.01 | Fazio, Albert et al. |
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| 5 | US 5754475 A | 12 | Bit line discharge method for reading a multiple bits-per-cell flash EEPROM | 365/185.25 | 365/185.2 | Bill, Colin et al. |
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